

# STARPOWER

SEMICONDUCTOR

# IGBT

## GD200HFT60C1S

Molding Type Module

600V/200A 2 in one-package

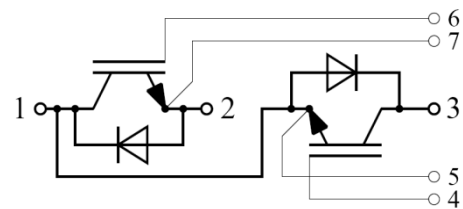
### General Description

STARPOWER IGBT Power Module provides ultra low conduction loss as well as short circuit ruggedness. They are designed for the applications such as UPS and SMPS.



### Features

- Low  $V_{CE(sat)}$  trench IGBT technology
- 5 $\mu$ s short circuit capability
- $V_{CE(sat)}$  with positive temperature coefficient
- Maximum junction temperature 175 $^{\circ}$ C
- Low inductance case
- Fast & soft reverse recovery anti-parallel FWD
- Isolated copper baseplate using DBC technology



Equivalent Circuit Schematic

### Typical Applications

- Electronic welders
- Switching mode power supplies
- Uninterruptible power supply

**Absolute Maximum Ratings**  $T_C=25^{\circ}\text{C}$  unless otherwise noted

Symbol	Description	GD200HFT60C1S	Units
$V_{CES}$	Collector-Emitter Voltage	600	V
$V_{GES}$	Gate-Emitter Voltage	$\pm 20$	V
$I_C$	Collector Current @ $T_C=25^{\circ}\text{C}$	305	A
	@ $T_C=80^{\circ}\text{C}$	200	
$I_{CM}$	Pulsed Collector Current $t_p=1\text{ms}$	400	A
$I_F$	Diode Continuous Forward Current @ $T_C=80^{\circ}\text{C}$	200	A
$I_{FM}$	Diode Maximum Forward Current $t_p=1\text{ms}$	400	A
$P_D$	Maximum Power Dissipation @ $T_j=175^{\circ}\text{C}$	765	W
$T_{jmax}$	Maximum Junction Temperature	175	$^{\circ}\text{C}$
$T_{jop}$	Operating Junction Temperature	-40 to +150	$^{\circ}\text{C}$
$T_{STG}$	Storage Temperature Range	-40 to +125	$^{\circ}\text{C}$
$V_{ISO}$	Isolation Voltage RMS, $f=50\text{Hz}, t=1\text{min}$	2500	V
Mounting Torque	Power Terminal Screw:M5 Mounting Screw:M6	2.5 to 5.0 3.0 to 5.0	N.m

**Electrical Characteristics of IGBT**  $T_C=25^{\circ}\text{C}$  unless otherwise noted**Off Characteristics**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$V_{(BR)CES}$	Collector-Emitter Breakdown Voltage	$T_j=25^{\circ}\text{C}$	600			V
$I_{CES}$	Collector Cut-Off Current	$V_{CE}=V_{CES}, V_{GE}=0\text{V},$ $T_j=25^{\circ}\text{C}$			5.0	mA
$I_{GES}$	Gate-Emitter Leakage Current	$V_{GE}=V_{GES}, V_{CE}=0\text{V},$ $T_j=25^{\circ}\text{C}$			400	nA

**On Characteristics**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	$I_C=2.0\text{mA}, V_{CE}=V_{GE},$ $T_j=25^{\circ}\text{C}$	4.0	4.4	6.5	V
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	$I_C=200\text{A}, V_{GE}=15\text{V},$ $T_j=25^{\circ}\text{C}$		1.65	2.10	V
		$I_C=200\text{A}, V_{GE}=15\text{V},$ $T_j=175^{\circ}\text{C}$		2.00		

**Switching Characteristics**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=300V, I_C=200A,$ $R_G=2.4\Omega, V_{GE}=\pm 15V,$ $T_j=25^\circ C$		136		ns
$t_r$	Rise Time			54		ns
$t_{d(off)}$	Turn-Off Delay Time			122		ns
$t_f$	Fall Time			87		ns
$E_{on}$	Turn-On Switching Loss			1.79		mJ
$E_{off}$	Turn-Off Switching Loss			1.99		mJ
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=300V, I_C=200A,$ $R_G=2.4\Omega, V_{GE}=\pm 15V,$ $T_j=125^\circ C$		145		ns
$t_r$	Rise Time			70		ns
$t_{d(off)}$	Turn-Off Delay Time			170		ns
$t_f$	Fall Time			112		ns
$E_{on}$	Turn-On Switching Loss			3.06		mJ
$E_{off}$	Turn-Off Switching Loss			3.62		mJ
$C_{ies}$	Input Capacitance	$V_{CE}=30V, f=1Mhz,$ $V_{GE}=0V$		15.4		nF
$C_{oes}$	Output Capacitance			2.60		nF
$C_{res}$	Reverse Transfer Capacitance			1.36		nF
$Q_G$	Gate Charge	$V_{CC}=400V, I_C=200A,$ $V_{GE}=15V$		417		nC
$R_{Gint}$	Internal Gate Resistance			2.5		$\Omega$
$I_{SC}$	SC Data	$t_p \leq 5\mu s, V_{GE}=15V,$ $T_j=125^\circ C, V_{CC}=360V,$ $V_{CEM} \leq 600V$		1800		A
$L_{CE}$	Stray Inductance				20	nH
$R_{CC'+EE'}$	Module Lead Resistance, Terminal To Chip			0.35		m $\Omega$

**Electrical Characteristics of Diode**  $T_C=25^\circ C$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$V_F$	Diode Forward Voltage	$I_F=200A,$ $V_{GE}=0V$	$T_j=25^\circ C$	1.40	1.80	V
			$T_j=125^\circ C$	1.40		
$Q_r$	Recovered Charge	$I_F=200A,$ $V_R=300V,$ $R_G=2.4\Omega,$ $V_{GE}=-15V$	$T_j=25^\circ C$	9.6		$\mu C$
			$T_j=125^\circ C$	13.0		
$I_{RM}$	Peak Reverse Recovery Current	$I_F=200A,$ $V_R=300V,$ $R_G=2.4\Omega,$ $V_{GE}=-15V$	$T_j=25^\circ C$	120		A
			$T_j=125^\circ C$	157		
$E_{rec}$	Reverse Recovery Energy	$I_F=200A,$ $V_R=300V,$ $R_G=2.4\Omega,$ $V_{GE}=-15V$	$T_j=25^\circ C$	1.88		mJ
			$T_j=125^\circ C$	3.62		

**Thermal Characteristics**

<b>Symbol</b>	<b>Parameter</b>	<b>Typ.</b>	<b>Max.</b>	<b>Units</b>
$R_{\theta JC}$	Junction-to-Case (per IGBT)		0.196	K/W
$R_{\theta JC}$	Junction-to-Case (per Diode)		0.350	K/W
$R_{\theta CS}$	Case-to-Sink (Conductive grease applied)	0.05		K/W
Weight	Weight of Module	150		g

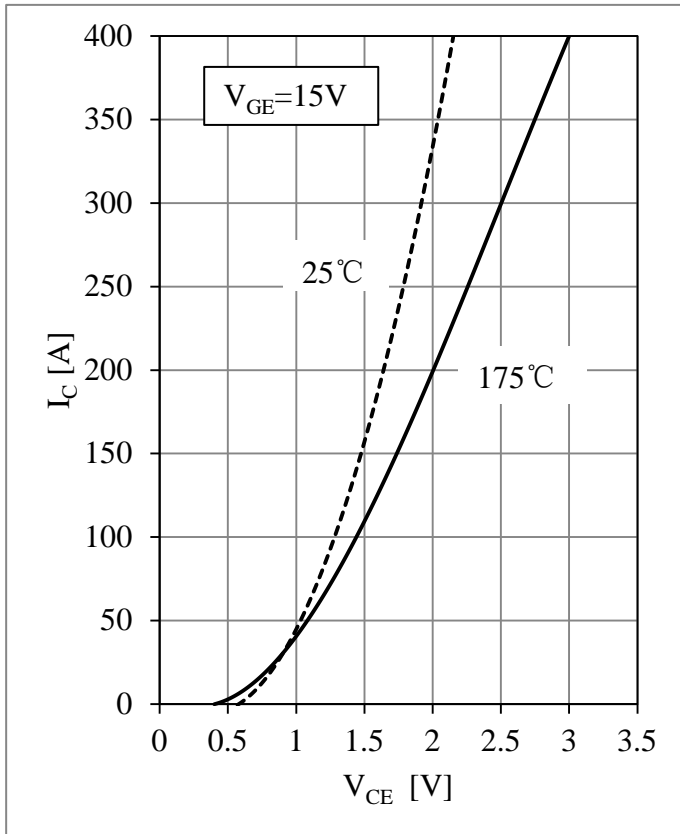


Fig 1. IGBT Output Characteristic

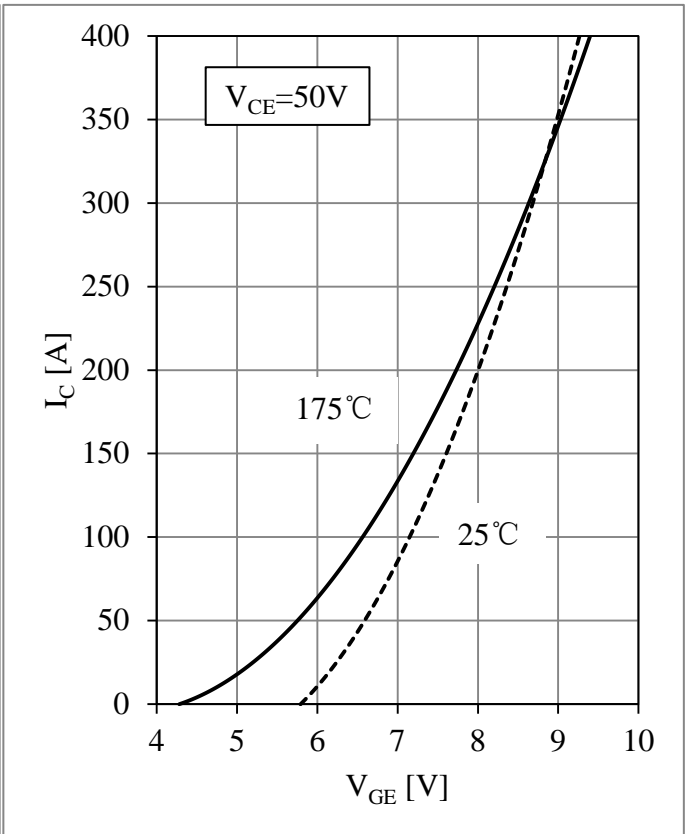


Fig 2. IGBT Transfer Characteristic

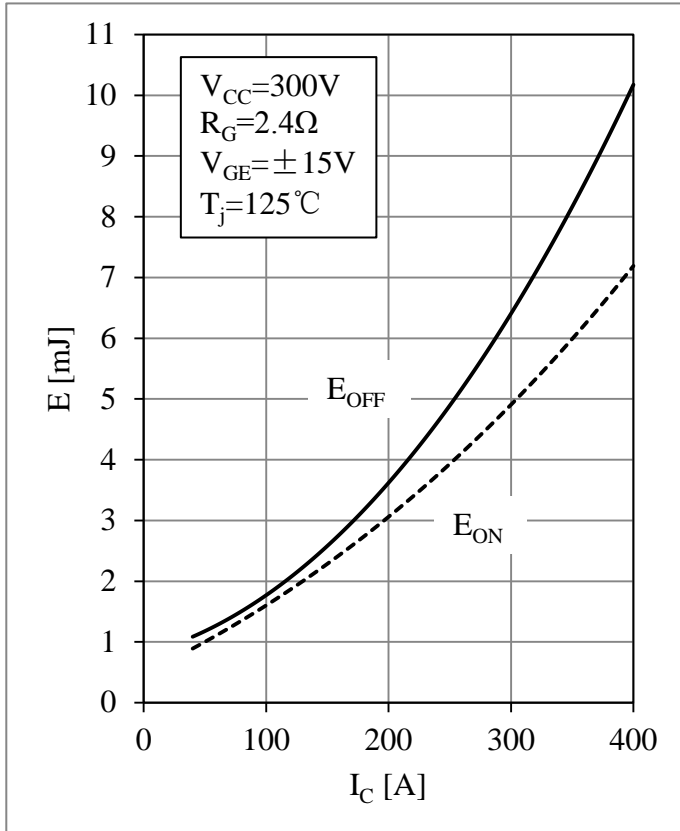


Fig 3. IGBT Switching Loss vs.  $I_C$

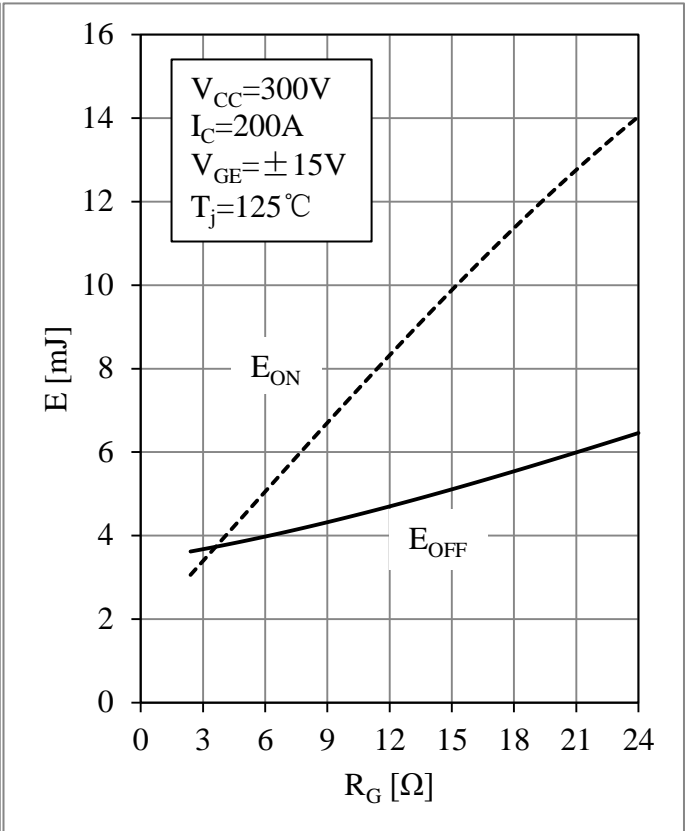


Fig 4. IGBT Switching Loss vs.  $R_G$

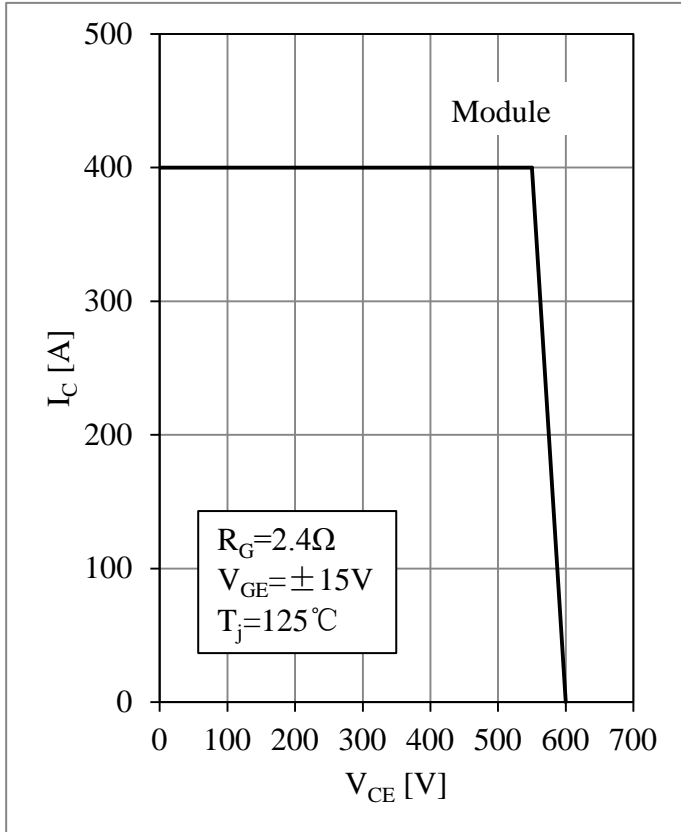


Fig 5. RBSOA

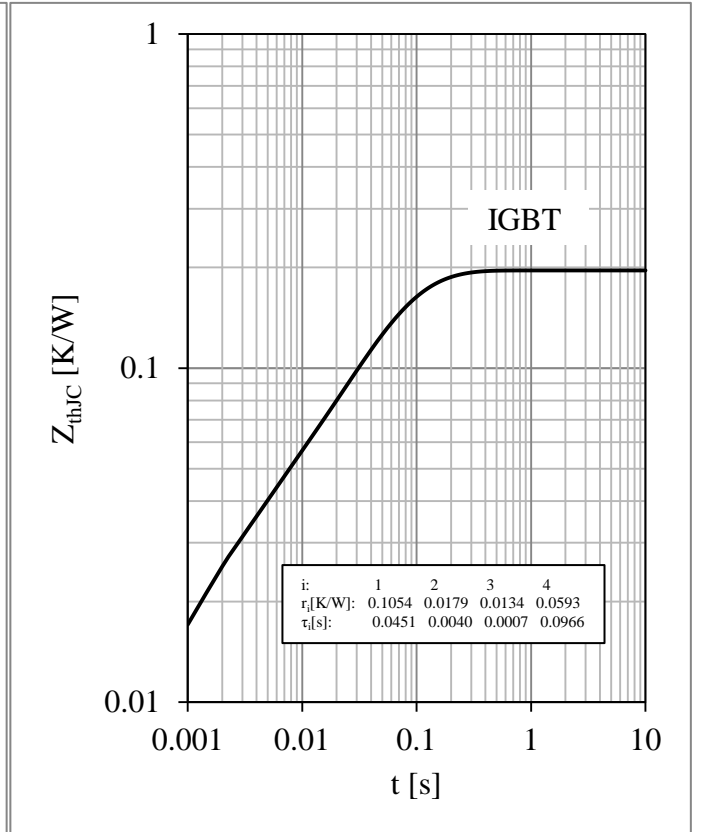


Fig 6. IGBT Transient Thermal Impedance

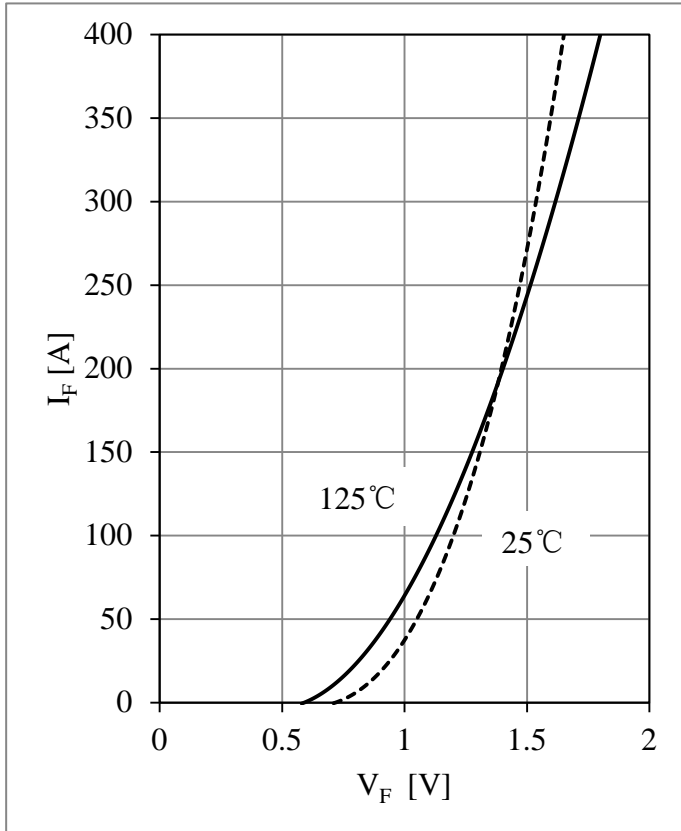


Fig 7. Diode Forward Characteristic

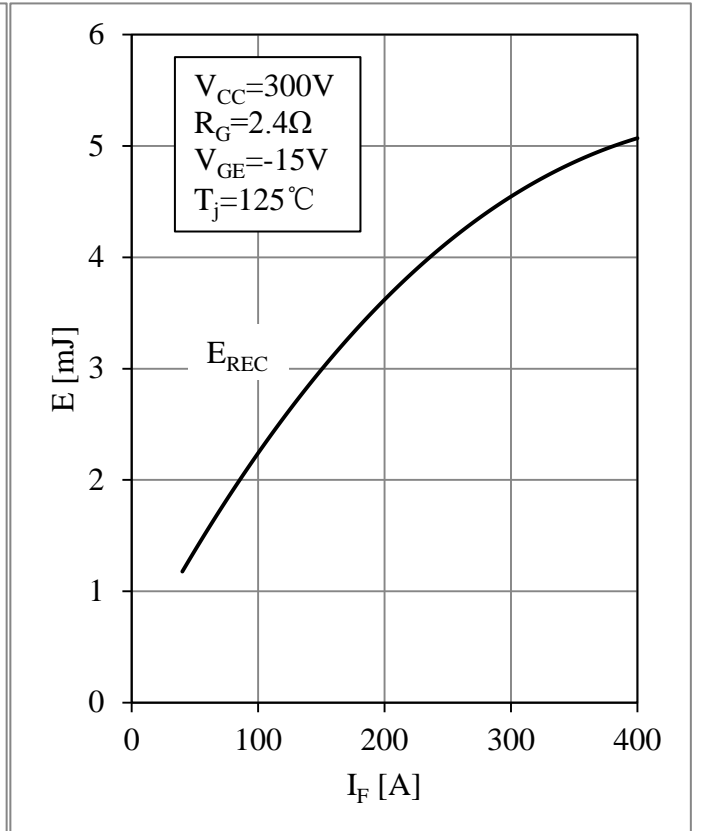


Fig 8. Diode Switching Loss vs.  $I_F$

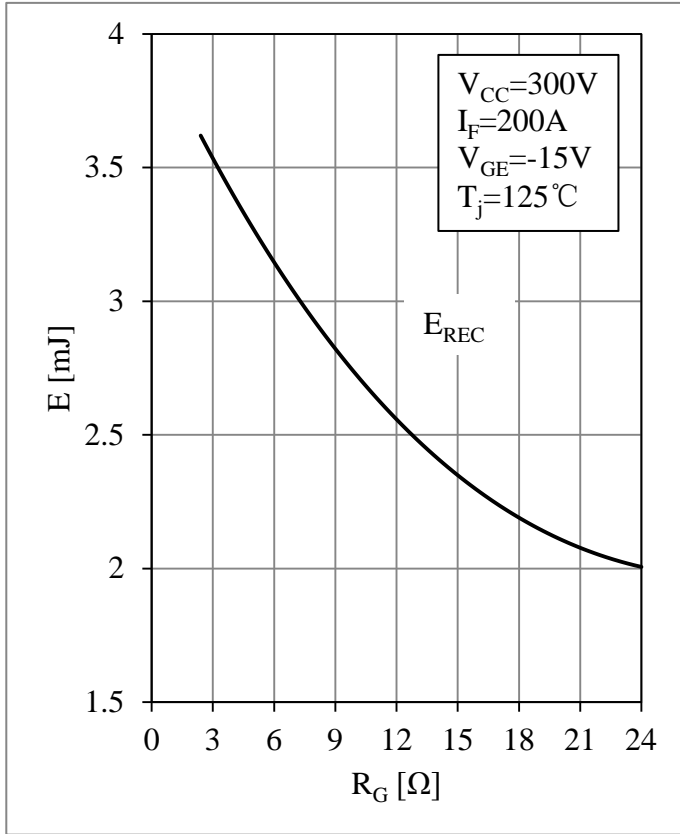


Fig 9. Diode Switching Loss vs.  $R_G$

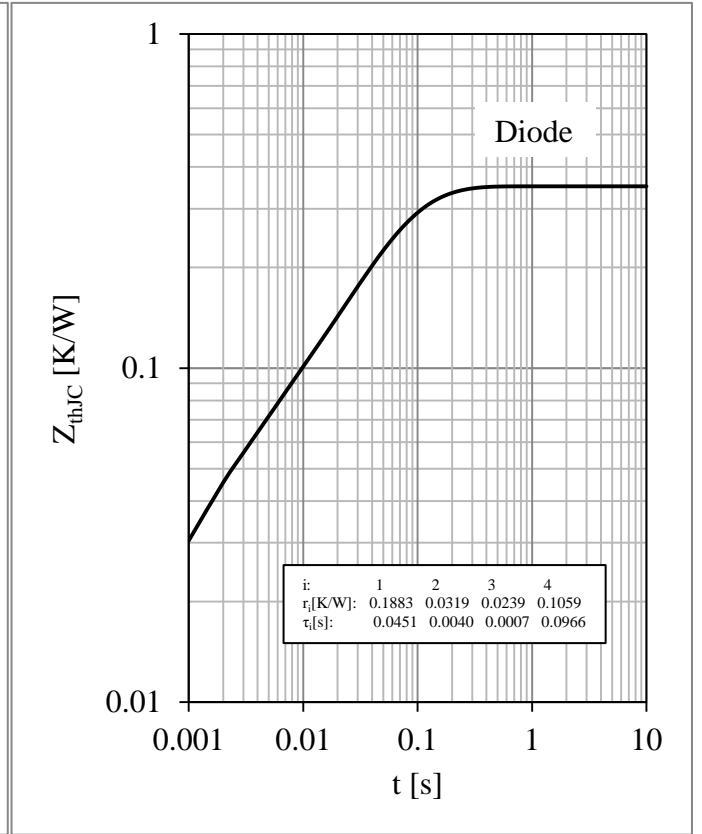
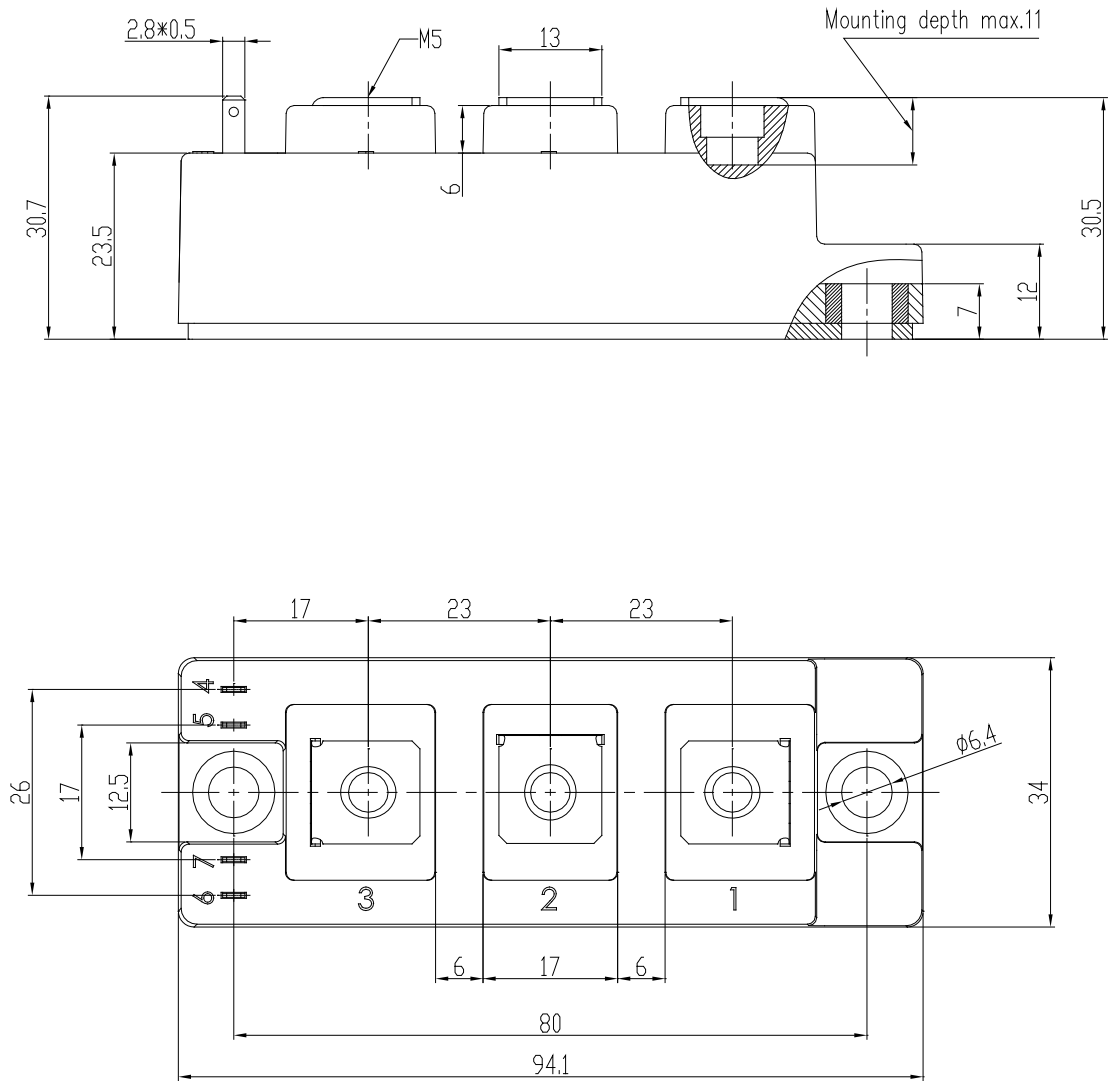


Fig 10. Diode Transient Thermal Impedance

### Package Dimensions

Dimensions in Millimeters





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